

ABSTRACT

The template type substrate is used for opto-electric or electrical devices and comprises A) a layer of bulk mono-crystal nitride containing at least one element of alkali metals (Group I, IUPAC 1989) and B) a layer of nitride grown by means of vapor phase epitaxy growth wherein the layer A) and the layer B) are combined at non N-polar face of the layer A) and N-polar face of the layer B). Therefore, the template type substrate has a good dislocation density and a good value of FWHM of the X-ray rocking curve from (0002) plane less than 80, so that the resulting template type substrate is very useful for the epitaxy substrate from gaseous phase such as MOCVD, MBE and HVPE, resulting in possibility of making good opto-electric devices such as Laser Diode and large-output LED and good electric devices such as MOSFET.